

40V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

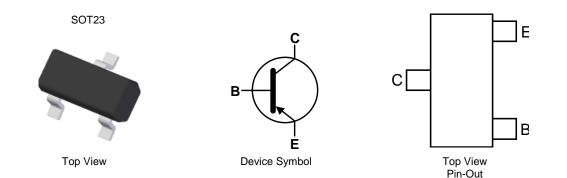
- BV_{CEO} > -40V
- I_C = -2A high Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ $I_C = -1A$.
- R_{CE(SAT)} = 90mΩ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary NPN Type: DSS4240T
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (Approximate)

Application

- Gate Driving MOSFETs and IGBTs
- Load Switch
- DC-DC Converters
- Battery Charging



Ordering Information (Note 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5240T-7	AEC-Q101	ZP2	7	8	3,000
DSS5240T-13	AEC-Q101	ZP2	13	8	10,000
DSS5240TQ-7	Automotive	ZP2	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

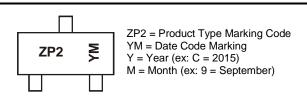
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Date Code K	ey											
Year	2013	2014	2015	2016	2017	2018	3 201	9 2	020	2021	2022	2023
Code	А	В	С	D	E	F	G	i	Н		J	К
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Collector Current	I _{CM}	-3	А
Continuous Collector Current	Ι _C	-2	А
Base Current	IB	-300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 6)	PD	730	mW	
Power Dissipation (Note 7)	PD	600	mW	
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{ ext{ heta}JA}$	171	°C/W	
Thermal Resistance, Junction to Ambient Air (Note 7)	R _{θJA}	209	°C/W	
Thermal Resistance, Junction to Lead (Note 8)	R _{θJL}	75	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

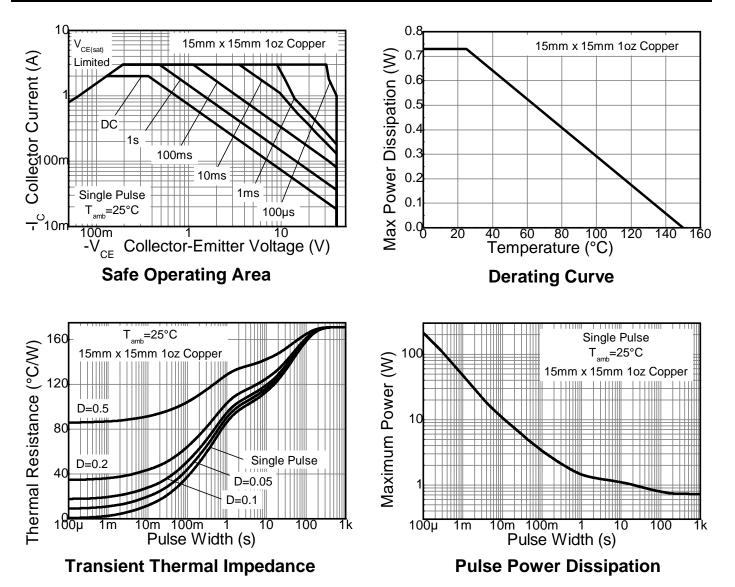
7. Same as note (6), except the device is mounted on minimum recommended pad layout.

8. Thermal resistance from junction to solder-point (at the end of the collector lead).

9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



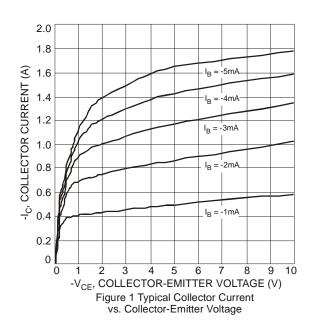


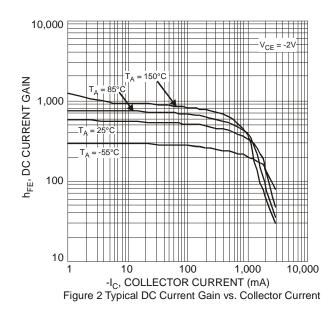
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS	e yser		.,,,	mux	onne	
Collector-Base Breakdown Voltage	BV _{CBO}	-40			V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)		-40		_	V	I _C = -10mA
Emitter-Base Breakdown Voltage		-5			V	I _E = -100μA
				-100	nA	$V_{CB} = -30V, I_E = 0$
Collector-Base Cutoff Current	I _{CBO}			-50	μA	$V_{CB} = -30V, I_E = 0, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
		300	_			$V_{CE} = -2V, I_{C} = -0.1A$
DC Current Gain	h	260	_			$V_{CE} = -2V, I_{C} = -0.5A$
	h _{FE}	210	—			$V_{CE} = -2V, I_{C} = -1A$
		100	—			$V_{CE} = -2V, I_{C} = -2A$
				-100		$I_{C} = -100 \text{mA}, I_{B} = -1 \text{mA}$
			45	-110	mV	$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_		-225		$I_{C} = -750 \text{mA}, I_{B} = -15 \text{mA}$
		_		-225		I _C = -1A, I _B = -50mA
		_		-350		$I_{C} = -2A, I_{B} = -200mA$
Equivalent On-Resistance	R _{CE(SAT)}		90	220	mΩ	$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.1	V	$I_{\rm C} = -2A, I_{\rm B} = -200 {\rm mA}$
Base-Emitter Turn-on Voltage		_	_	-0.75	V	$V_{CE} = -2V, I_{C} = -100mA$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	_	_	MHz	V _{CE} = -10V, I _C = -100mA, f = 100MHz
Output Capacitance	C _{ob}			28	pF	V _{CB} = -10V, f = 1MHz

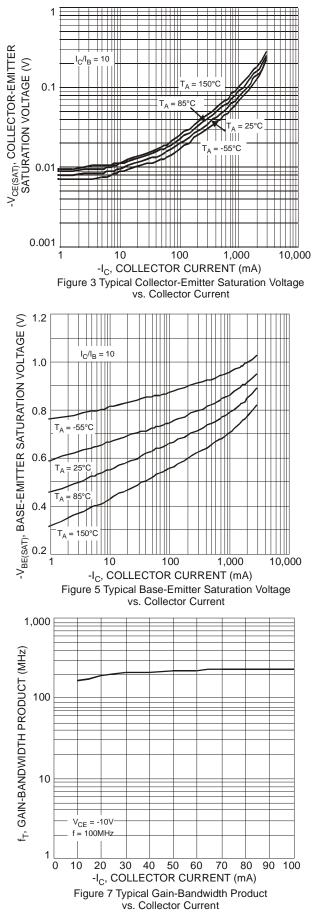
Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

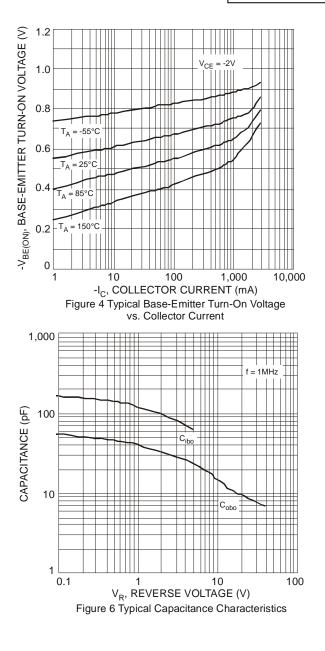
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







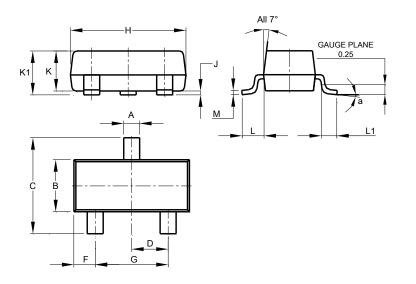






Package Outline Dimensions

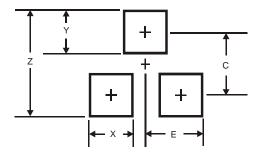
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	a 8°						
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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